

ABSTRACT OF THE DISCLOSURE

A MOSFET includes a double silicided source/drain structure wherein the source/drain terminals include a silicided source/drain extension, a deep silicided
5 source/drain region, and a doped semiconductor portion that surrounds a portion of the source/drain structure such that the silicides are isolated from the MOSFET body node. In a further aspect of the present invention, a barrier layer is formed around a gate electrode to prevent electrical shorts between a silicided source/drain extension and the gate electrode. A deep source/drain is then
10 formed, self-aligned to sidewall spacers that are formed subsequent to the silicidation of the source/drain extension.

550E90" E62E4E60